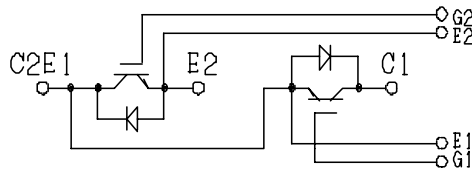


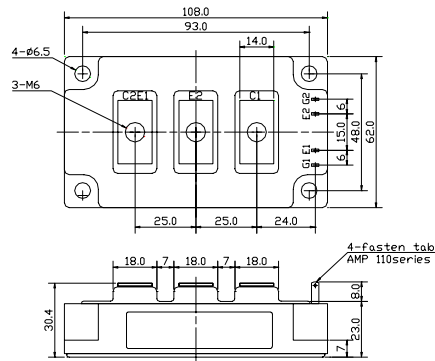
IGBT MODULE Dual 200A 1200V

PDMB200B12C

CIRCUIT



OUTLINE DRAWING



4- fasten- tab No 110

Dimension(mm)

Approximate Weight : 500g

MAXMUM RATINGS (Tc=25°C)

Item		Symbol	PDMB200B12C	Unit
Collector-Emitter Voltage		V _{CES}	1200	V
Gate - Emitter Voltage		V _{GES}	+/- 20	V
Collector Current	DC	I _C	200	A
	1 ms	I _{CP}	400	
Collector Power Dissipation		P _C	960	W
Junction Temperature Range		T _j	-40 to +150	°C
Storage Temperature Range		T _{stg}	-40 to +125	°C
Isolation Voltage Terminal to Base AC, 1 min.)		V _{ISO}	2500	V
Mounting Torque	Module Base to Heatsink	F _{TOR}	3	N•m
	Bus Bar to Main Terminals			

ELECTRICAL CHARACTERISTICS (Tc=25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter Cut-Off Current		I _{CES}	V _{CE} =1200V, V _{GE} =0V	-	-	4.0	mA
Gate-Emitter Leakage Current		I _{GES}	V _{GE} =+/- 20V, V _{CE} =0V	-	-	1.0	μA
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =200A, V _{GE} =15V	-	1.9	2.4	V
Gate-Emitter Threshold Voltage		V _{GE(th)}	V _{CE} =5V, I _C =200mA	4.0	-	8.0	V
Input Capacitance		C _{ies}	V _{CE} =10V, V _{GE} =0V, f=1MHz	-	16600	-	pF
Switching Time	Rise Time	t _r	V _{CC} = 600V	-	0.25	0.45	μs
	Turn-on Time	t _{on}	R _L = 3 ohm	-	0.40	0.70	
	Fall Time	t _f	R _G = 2 ohm	-	0.25	0.35	
	Turn-off Time	t _{off}	V _{GE} = +/- 15V	-	0.80	1.10	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (Tc=25°C)

Item		Symbol	Rated Value	Unit
Forward Current	DC	I _F	200	A
	1 ms	I _{FM}	400	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V _F	I _F =200A, V _{GE} =0V	-	1.9	2.4	V
Reverse Recovery Time	t _{rr}	I _F =200A, V _{GE} =-10V, di/dt=400A/μs	-	0.2	0.3	μs

THERMAL CHARACTERISTICS

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	R _{th(j-c)}	Junction to Case	-	-	0.125	°C/W
	DIODE			-	-	0.24	

PDMB200B12C

Fig.1- Output Characteristics (Typical)

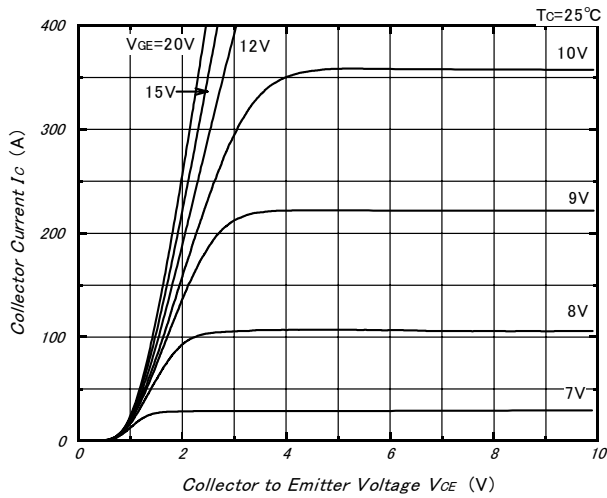


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

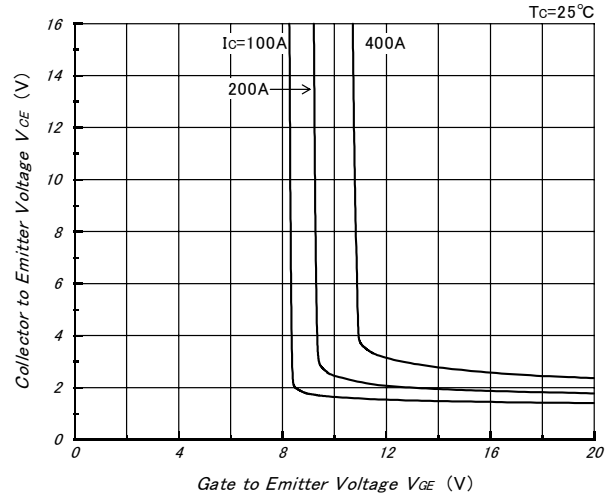


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

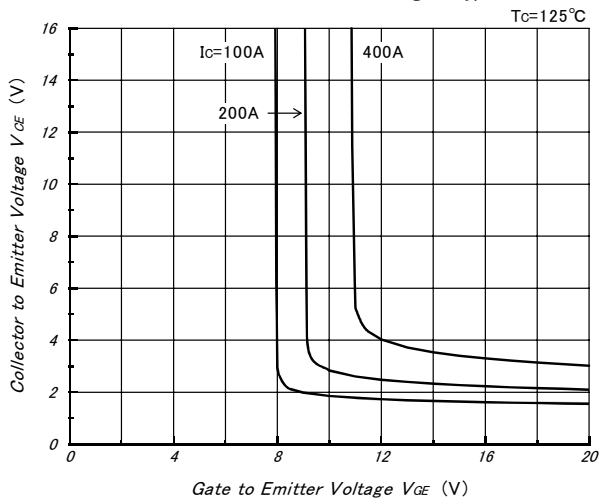


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

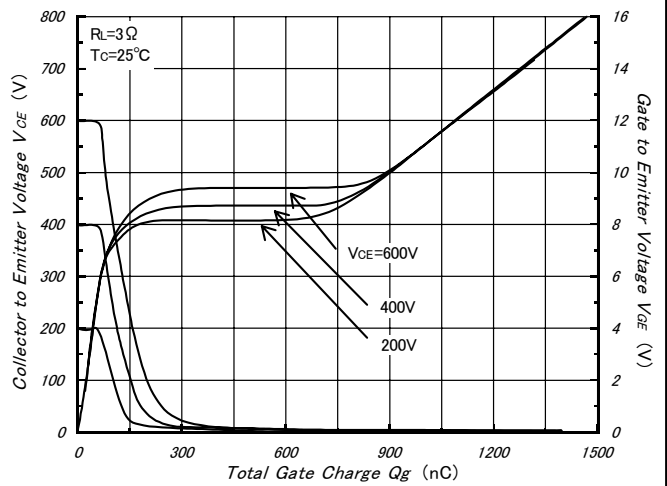


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

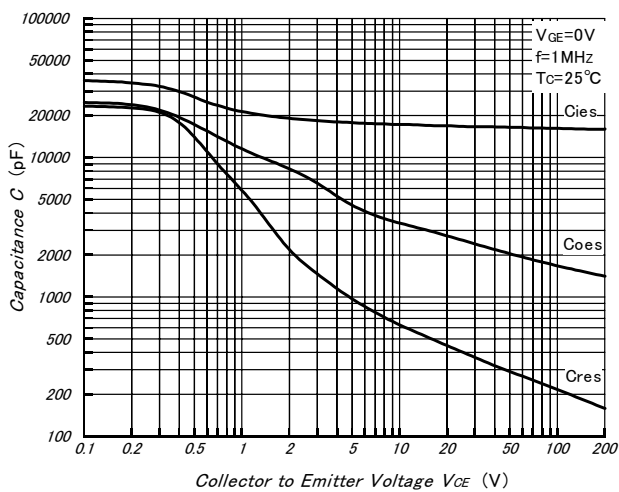
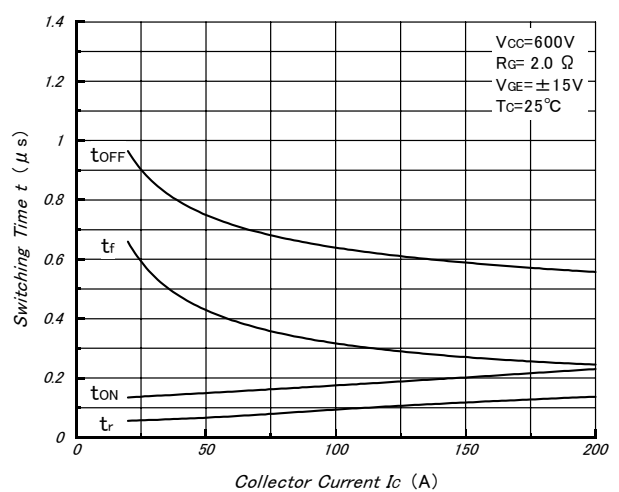


Fig.6- Collector Current vs. Switching Time (Typical)



PDMB200B12C

Fig.7- Series Gate Impedance vs. Switching Time (Typical)

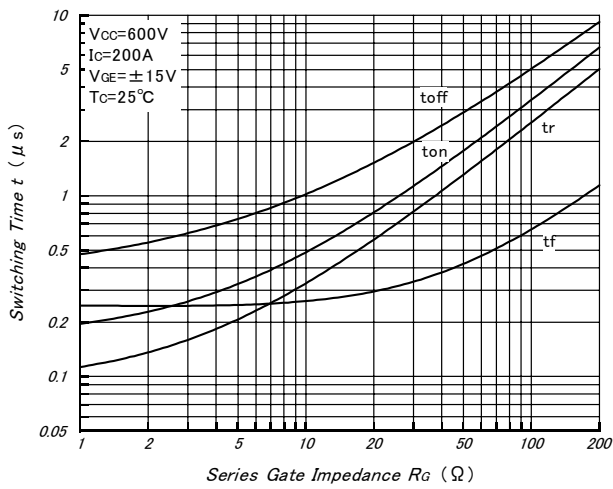


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

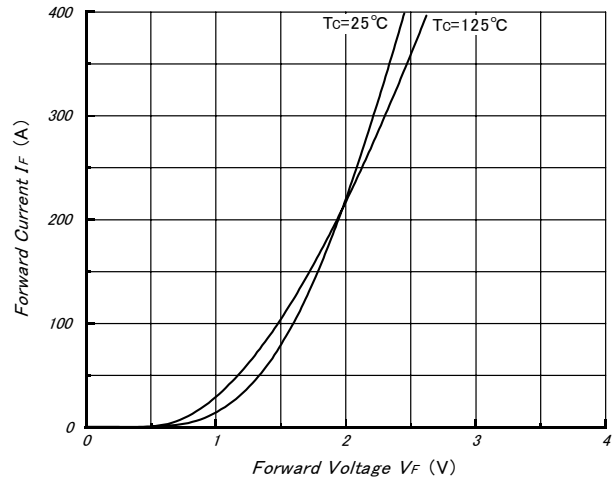


Fig.9- Reverse Recovery Characteristics (Typical)

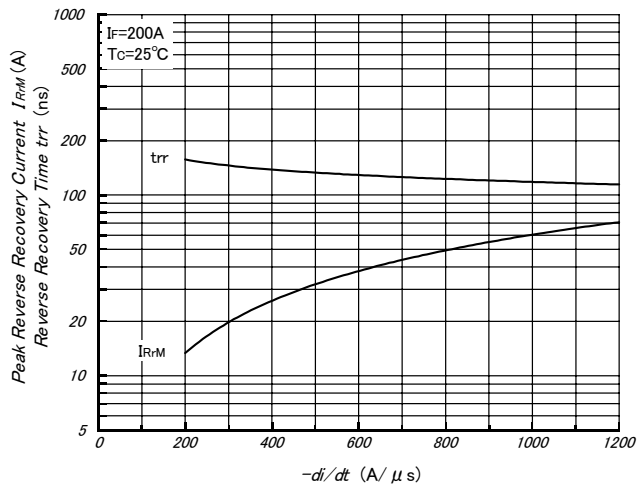


Fig.10- Reverse Bias Safe Operating Area (Typical)

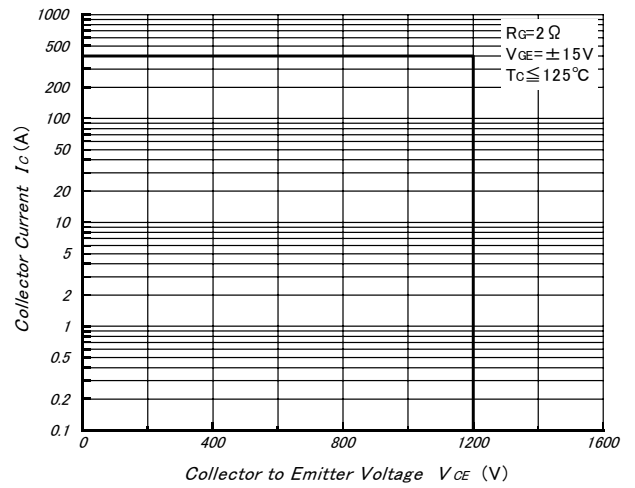


Fig.11- Transient Thermal Impedance

